



Integrated Device Technology, Inc.

CMOS STATIC RAM
16K (16K x 1-BIT)
IDT6167SA
IDT6167LA

T-46-23-05

FEATURES:

- High-speed (equal access and cycle time)
 - Military: 15/20/25/35/45/55/70/85/100ns (max.)
 - Commercial: 12/15/20/25/35ns (max.)
- Low power consumption
- Battery backup operation — 2V data retention voltage (IDT6167LA only)
- Available in 20-pin Cerdip and Plastic DIP, 20-pin CERPACK, 20-pin SOIC and 20-pin leadless chip carrier
- Produced with advanced CMOS high-performance technology
- CMOS process virtually eliminates alpha particle soft-error rates
- Separate data input and output
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION:

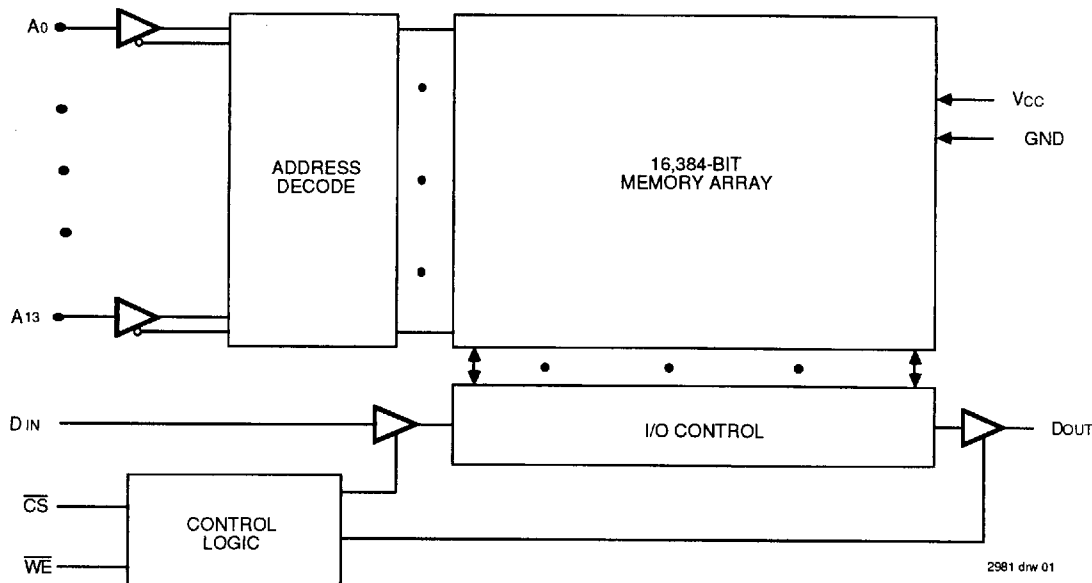
The IDT6167 is a 16,384-bit high-speed static RAM organized as 16K x 1. The part is fabricated using IDT's high-performance, high reliability CMOS technology.

Access times as fast as 12ns are available. The circuit also offers a reduced power standby mode. When $\overline{CS}$ goes HIGH, the circuit will automatically go to, and remain in, a standby mode as long as $\overline{CS}$ remains HIGH. This capability provides significant system-level power and cooling savings. The low-power (LA) version also offers a battery backup data retention capability where the circuit typically consumes only 1 μ W operating off a 2V battery.

All inputs and the output of the IDT6167 are TTL-compatible and operate from a single 5V supply, thus simplifying system designs.

The IDT6167 is packaged in a space-saving 20-pin, 300 mil Plastic DIP or Cerdip, Plastic 20-pin SOIC or SOJ, 20-pin CERPACK and 20-pin leadless chip carrier, providing high board-level packing densities.

Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

FUNCTIONAL BLOCK DIAGRAM

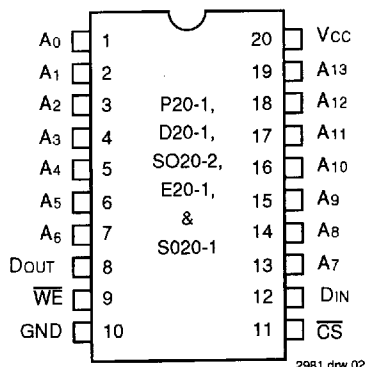
The IDT logo is a registered trademark of Integrated Device Technology, Inc.

MILITARY AND COMMERCIAL TEMPERATURE RANGES**AUGUST 1992**

IDT6167SA/LA
CMOS STATIC RAM 16K (16K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

PIN CONFIGURATIONS



DIP/SOIC/CERPACK/SOJ
TOP VIEW

PIN NAMES

A ₀ -A ₁₃	Address Inputs
$\overline{CS}$	Chip Select
WE	Write Enable
V _{CC}	Power
DIN	DATAin
DOUT	DATAOUT
GND	Ground

2981 tbl 01

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V _{IH}	Input High Voltage	2.2	—	6.0	V
V _{IL}	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

NOTE:

2981 tbl 05

1. V_{IL} (min.) = -3.0V for pulse width less than 20ns, once per cycle.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	V _{CC}
Military	-55°C to +125°C	0V	5V ± 10%
Commercial	0°C to +70°C	0V	5V ± 10%

2981 tbl 06

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	7	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	7	pF

NOTE:

2981 tbl 04

1. This parameter is determined by device characterization, but is not production tested.

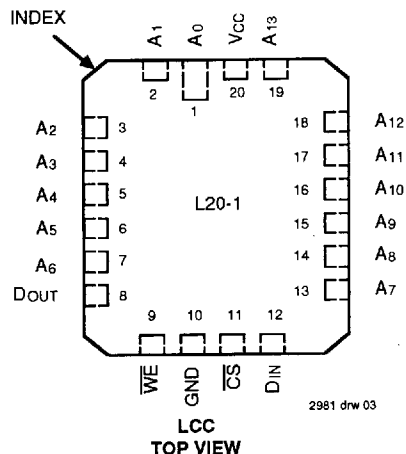
TRUTH TABLE ⁽¹⁾

Mode	CS	WE	Output	Power
Standby	H	X	High-Z	Standby
Read	L	H	DATAOUT	Active
Write	L	L	High-Z	Active

NOTE:

2981 tbl 02

1. H = V_{IH}, L = V_{IL}, X = Don't Care.



LCC
TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Com'l.	Mil.	Unit
V _{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
T _A	Operating Temperature	0 to +70	-55 to +125	°C
T _{BIAS}	Temperature Under Bias	-55 to +125	-65 to +135	°C
T _{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P _T	Power Dissipation	1.0	1.0	W
I _{OUT}	DC Output Current	50	50	mA

NOTE:

2981 tbl 03

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS⁽¹⁾(VCC = 5.0V ± 10%, V_{LC} = 0.2V, V_{HC} = VCC - 0.2V)

Symbol	Parameter	Power	6167SA12		6167SA/LA15		6167SA/LA20		6167SA/LA25		Unit
			Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
ICC1	Operating Power Supply Current CS ≤ V _{IL} , Outputs Open, VCC = Max., f = 0 ⁽³⁾	SA	90	—	90	90	90	90	90	90	mA
		LA	—	—	55	60	55	60	55	60	
ICC2	Dynamic Operating Current CS ≤ V _{IL} , Outputs Open, VCC = Max., f = f _{MAX} ⁽³⁾	SA	140	—	120	130	100	110	100	100	mA
		LA	—	—	100	110	80	85	70	75	
ISB	Standby Power Supply Current (TTL Level) CS ≥ V _{IH} , Outputs Open, VCC = Max., f = f _{MAX} ⁽³⁾	SA	50	—	50	50	35	35	35	35	mA
		LA	—	—	35	35	30	30	25	25	
ISB1	Full Standby Power Supply Current (CMOS Level) CS ≥ V _{HC} , VCC = Max. VIN ≥ V _{HC} or VIN ≤ V _{LC} , f = 0 ⁽³⁾	SA	10	—	5	10	5	10	5	10	mA
		LA	—	—	0.9	2	0.05	2	0.05	0.9	

DC ELECTRICAL CHARACTERISTICS⁽¹⁾ (CONTINUED)(VCC = 5.0V ± 10%, V_{LC} = 0.2V, V_{HC} = VCC - 0.2V)

Symbol	Parameter	Power	6167SA/LA35		6167SA/LA45 ⁽²⁾		6167SA/LA55 ⁽²⁾		6167SA/LA70 ⁽²⁾		Unit
			Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
ICC1	Operating Power Supply Current CS ≤ V _{IL} , Outputs Open, VCC = Max., f = 0 ⁽³⁾	SA	90	90	—	90	—	90	—	90	mA
		LA	55	60	—	60	—	60	—	60	
ICC2	Dynamic Operating Current CS ≤ V _{IL} , Outputs Open, VCC = Max., f = f _{MAX} ⁽³⁾	SA	100	100	—	100	—	100	—	100	mA
		LA	65	70	—	65	—	60	—	60	
ISB	Standby Power Supply Current (TTL Level) CS ≥ V _{IH} , Outputs Open, VCC = Max., f = f _{MAX} ⁽³⁾	SA	35	35	—	35	—	35	—	35	mA
		LA	20	20	—	20	—	20	—	15	
ISB1	Full Standby Power Supply Current (CMOS Level) CS ≥ V _{HC} , VCC = Max. VIN ≥ V _{HC} or VIN ≤ V _{LC} , f = 0 ⁽³⁾	SA	5	10	—	10	—	10	—	10	mA
		LA	0.05	0.9	—	0.9	—	0.9	—	0.9	

NOTES:

- All values are maximum guaranteed values.
- 55°C to +125°C temperature range only. Also available; 85ns and 100ns Military devices.
- f_{MAX} = 1/TRC, only address inputs cycling at f_{MAX}. f = 0 means no Address inputs change.

2980 tcl 07

IDT6167SA/LA
CMOS STATIC RAM 16K (16K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

DC ELECTRICAL CHARACTERISTICS

$V_{CC} = 5.0V \pm 10\%$

VCC = 5.0V ± 10%

Symbol	Parameter	Test Condition		IDT6167SA		IDT6167LA		Unit
				Min.	Max.	Min.	Max.	
ILI	Input Leakage Current	VCC = Max., VIN = GND to VCC	MIL	—	10	—	5	μA
			COM'L	—	5	—	2	
ILO	Output Leakage Current	VCC = Max., CS = VIH, VOUT = GND to VCC	MIL	—	10	—	5	μA
			COM'L	—	5	—	2	
VOL	Output Low Voltage	IOL = 8mA, VCC = Min.		—	0.4	—	0.4	V
VOH	Output High Voltage	IOL = -4mA, VCC = Min.		2.4	—	2.4	—	V

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES

(L Version Only) $V_{LC} = 0.2V, V_{HC} = V_{CC} - 0.2V$

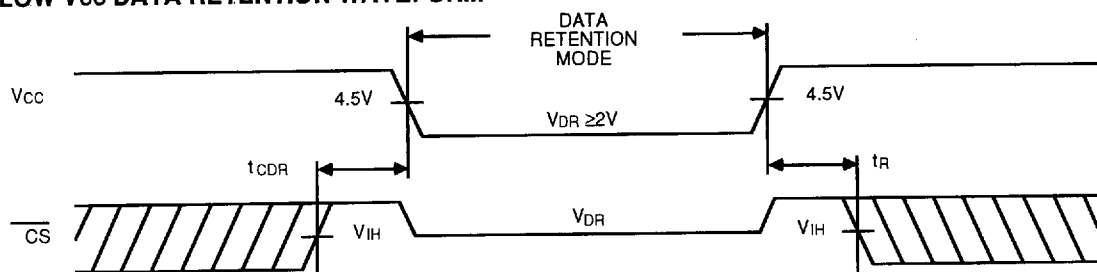
Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾ V _{CC} @		Max. V _{CC} @		Unit
				2.0v	3.0V	2.0V	3.0V	
V _{DR}	V _{CC} for Data Retention	—	2.0	—	—	—	—	V
I _{CCDR}	Data Retention Current	MIL. COM'L.	—	0.5	1.0	200	300	μA
			—	0.5	1.0	20	30	
t _{CDR}	Chip Deselect to Data Retention Time	$\overline{\text{CS}} \geq V_{HC}$ $V_{IN} \geq V_{HC} \text{ or } \leq V_{LC}$	0	—	—	—	—	ns
t _R ⁽³⁾	Operation Recovery Time	t _{RC} ⁽²⁾	—	—	—	—	—	ns
I _{LI} ⁽³⁾	Input Leakage Current	—	—	—	—	2	2	μA

2981 tbi 09

NOTES:

1. $T_A = +25^\circ\text{C}$.
2. t_{RC} = Read Cycle Time.
3. This parameter is guaranteed by device characterization, but is not production tested.

LOW V_{CC} DATA RETENTION WAVEFORM



2981 drw 04

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

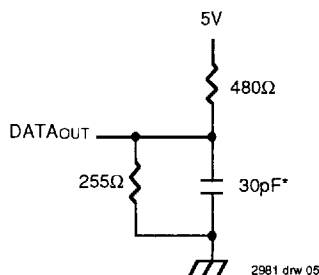
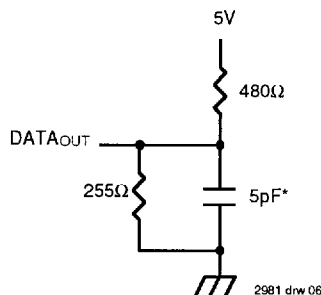


Figure 1. AC Test Load

Figure 2. AC Test Load
(for tCLZ, tCHZ, tWHZ and tOW)

*Includes scope and jig.

AC ELECTRICAL CHARACTERISTICS (VCC = 5.0V ± 10%, All Temperature Ranges)

Symbol	Parameter	6167SA12 ⁽¹⁾		6167SA15 6167LA15		6167SA20/25 6167LA20/25		6167SA35/45 ⁽²⁾ 6167LA35/45 ⁽²⁾		6167SA55 ^{(2)/70⁽²⁾ 6167LA55^{(2)/70⁽²⁾}}		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle												
tRC	Read Cycle Time	12	—	15	—	20/25	—	35/45	—	55/70	—	ns
tAA	Address Access Time	—	12	—	15	—	20/25	—	35/45	—	55/70	ns
tACS	Chip Select Access Time	—	12	—	15	—	20/25	—	35/45	—	55/70	ns
tCLZ	Chip Deselect to Output in Low-Z ⁽³⁾	3	—	3	—	5/5	—	5/5	—	5/5	—	ns
tCHZ	Chip Select to Output in High-Z ⁽³⁾	—	8	—	10	—	10/10	—	15/30	—	40/40	ns
tOH	Output Hold from Address Change	3	—	3	—	5/5	—	5/5	—	5/5	—	ns
tPU	Chip Select to Power-Up Time ⁽³⁾	0	—	0	—	0/0	—	0/0	—	0/0	—	ns
tPD	Chip Deselect to Power-Down Time ⁽³⁾	—	12	—	15	—	20/25	—	35/45	—	55/70	ns
Write Cycle												
tWC	Write Cycle Time	12	—	15	—	20/20	—	30/45	—	55/70	—	ns
tCW	Chip Select to End-of-Write	12	—	15	—	15/20	—	30/40	—	45/55	—	ns
tAW	Address Valid to End-of-Write	12	—	15	—	15/20	—	30/40	—	45/55	—	ns
tAS	Address Set-up Time	0	—	0	—	0/0	—	0/0	—	0/0	—	ns
tWP	Write Pulse Width	12	—	13	—	15/20	—	30/30	—	35/40	—	ns
tWR	Write Recovery Time	0	—	0	—	0/0	—	0/0	—	0/0	—	ns
tDW	Data Valid to End-of-Write	10	—	10	—	12/15	—	17/20	—	25/30	—	ns
tDH	Data Hold Time	0	—	0	—	0/0	—	0/0	—	0/0	—	ns
tWHZ	Write Enable to Output in High-Z ⁽³⁾	—	6	—	7	—	8/8	—	15/30	—	40/40	ns
tOW	Output Active from End-of-Write ⁽³⁾	0	—	0	—	0/0	—	0/0	—	0/0	—	ns

NOTES:

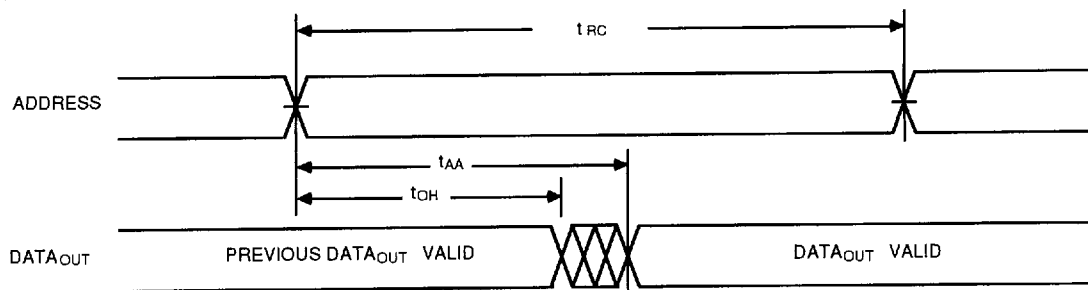
1. 0° to +70°C temperature range only.

2. -55°C to +125°C temperature range only. Also available: 85ns and 100ns Military devices.

3. This parameter is guaranteed with AC Load (Figure 2) by device characterization, but is not production tested.

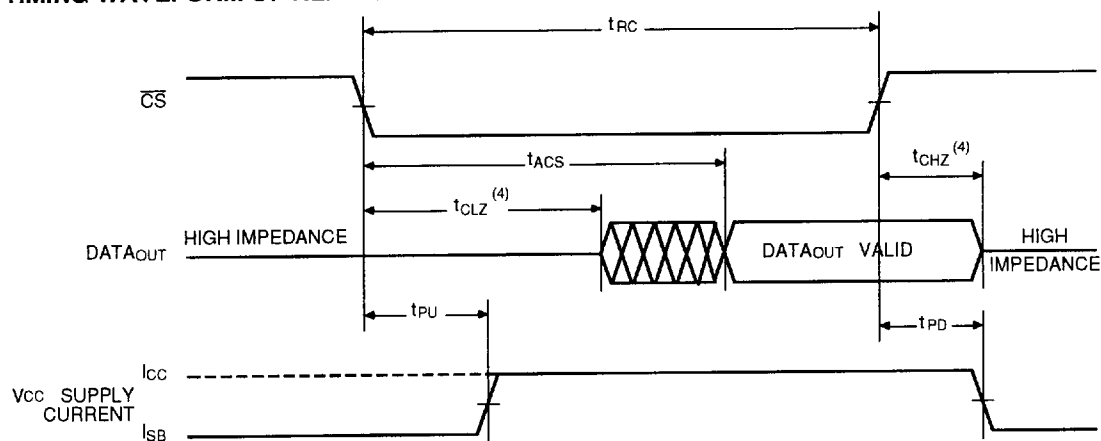
2981 tbl 11

TIMING WAVEFORM OF READ CYCLE NO. 1(1, 2)



2981 drw 07

TIMING WAVEFORM OF READ CYCLE NO. 2(1, 3)



2981 drw 08

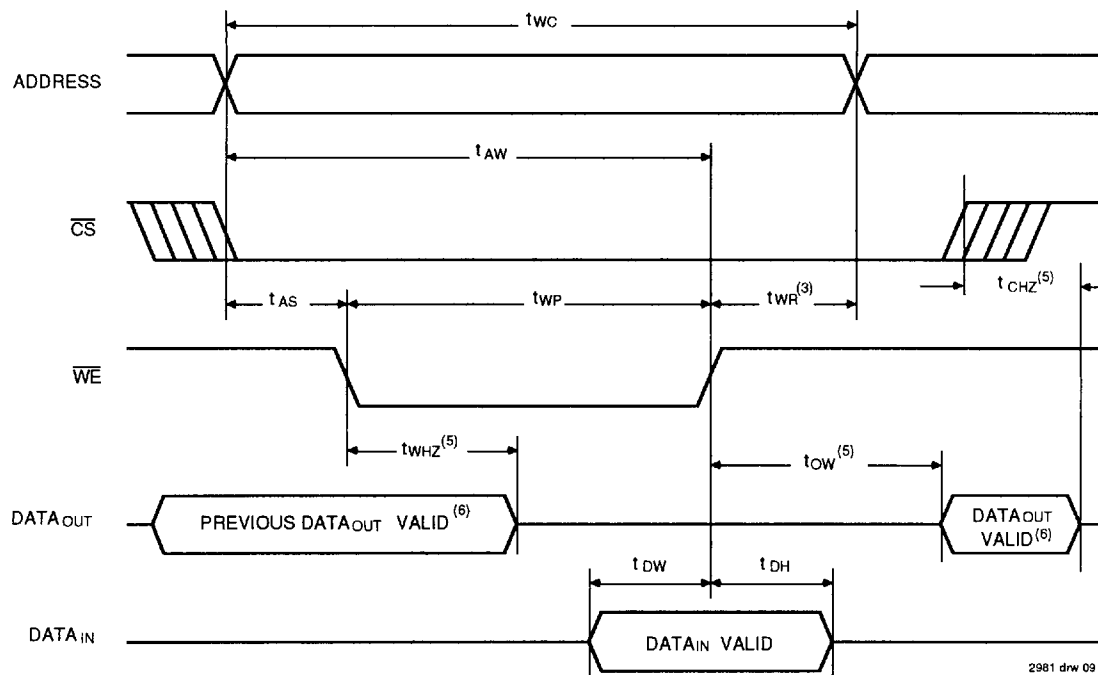
NOTES:

1. $\overline{WE}$ is HIGH for read cycle, $\overline{WE} \geq V_{IH}$
2. Device is continuously selected, $\overline{CS} \leq V_{IL}$
3. Address valid prior to or coincident with $\overline{CS}$ transition low.
4. Transition is measured $\pm 200\text{mV}$ from steady state.

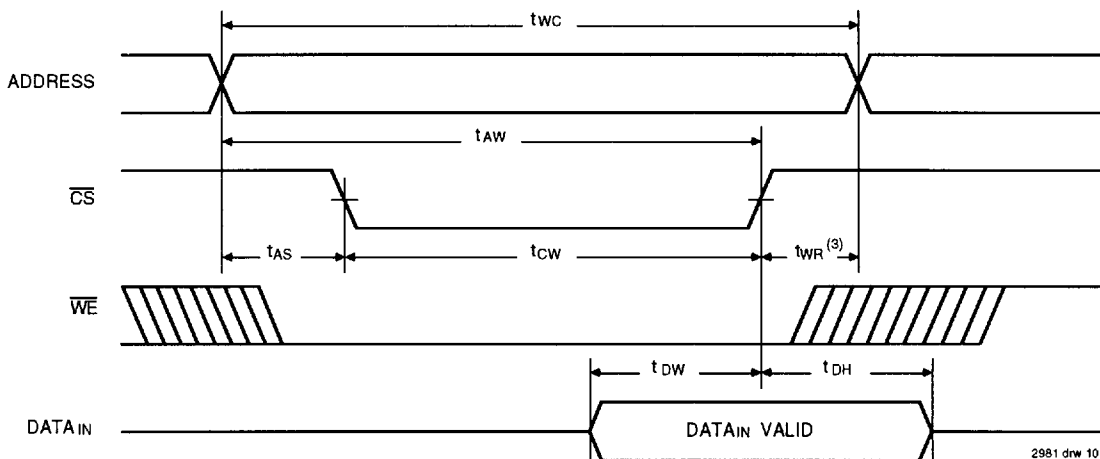
IDT6167SA/LA
CMOS STATIC RAM 16K (16K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

TIMING WAVEFORM OF WRITE CYCLE NO. 1, ($\overline{WE}$ CONTROLLED TIMING)^(1, 2, 4)



TIMING WAVEFORM OF WRITE CYCLE NO. 2, ($\overline{CS}$ CONTROLLED TIMING)^(1, 2, 4)



NOTES:

1. $\overline{WE}$ or $\overline{CS}$ must be inactive during all address transitions.
2. A write occurs during the overlap of a LOW $\overline{CS}$ and a LOW $\overline{WE}$.
3. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going HIGH to the end of the write cycle.
4. If the $\overline{CS}$ low transition occurs simultaneously with or after the $\overline{WE}$ LOW transition, the outputs remain in the high-impedance state.
5. Transition is measured $\pm 200\text{mV}$ from steady state.
6. During this period, the I/O pins are in the output state and the input signals must not be applied.

IDT6167SA/LA
CMOS STATIC RAM 16K (16K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

ORDERING INFORMATION

IDT	6167	X	XXX	XX	X		
	Device Type	Power	Speed	Package	Process/ Temperature Range		
						Blank	Commercial (0°C to +70°C)
						B	Military (-55°C to +125°C) Compliant to MIL-STD-883, Class B
						P	300MIL Plastic DIP (P20-1)
						D	300MIL CERDIP (D20-1)
						L	300MIL Leadless Chip Carrier (L20-1)
						SO	300MIL Small Outline IC (SO20-1)
						E	300MIL CERPACK (E20-1)
						Y	300MIL SOJ (SO24-4)
						12	Commercial Only
						15	Com'l and Mil.
						20	Com'l and Mil.
						25	Com'l and Mil.
						35	Com'l and Mil.
						45	Military Only
						55	Military Only
						70	Military Only
						85	Military Only
						100	Military Only
						SA	Standard Power
						LA	Low Power

Speed in Nanoseconds

2981 drw 11